

LED770-03AU

Infrared LED Lamp

LED770-03AU is an AlGaAs LED mounted on a lead frame with a clear epoxy lens. On forward bias, it emits a spectral band of radiation which peaks at 770 nm.

Specifications

1) Product Name Infrared LED Lamp 2) Type No. LED770-03AU

3) Chip

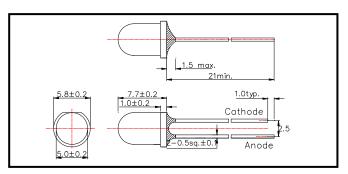
(1) Chip Material AlGaAs(2) Peak Wavelength 770 nm typ.

4) Package

(1) Type 5 mm clear molding

(2) Resin Material Epoxy Resin(3) Lead Frame Soldered

Outer dimension (Unit: mm)



Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value U		Ambient Temperature	
Power Dissipation	Po	190	mW	Ta = 25°C	
Forward Current	lF	100	mΑ	Ta = 25°C	
Pulse Forward Current	I FP	500	mΑ	Ta = 25°C	
Reverse Voltage	Vr	5	V	Ta = 25°C	
Operating Temperature	Topr	-30 ~ +85	°C		
Storage Temperature	Тѕтс	-30 ~ +100	°C		
Soldering Temperature	Tsol	260	°C		

[‡]Pulse Forward Current condition: Duty = 1% and Pulse Width = 10 μ s.

Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	$I_F = 50 \text{ mA}$		1.75	1.95	V
Reverse Current	lr	Vr = 5 V			10	uA
Total Radiated Power	Po	$I_F = 50 \text{ mA}$	13.0	18.0		mW
Radiant Intensity	ΙE	$I_F = 50 \text{ mA}$	18	35		mW/sr
Peak Wavelength	λР	$I_F = 50 \text{ mA}$	750	770	790	nm
Half Width	Δλ	$I_F = 50 \text{ mA}$		35		nm
Viewing Half Angle	. α	If = 50 mA		±15		deg.
Rise Time	tr	If = 50 mA		80		ns
Fall Time	tf	If = 50 mA		80		ns

[‡]Total Radiated Power is measured by Photodyne #500

[‡]Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

[‡]Radiant Intensity is measured by Tektronix J-6512